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2N6557
 2N6558
 2N6559
 NPN SILICON HIGH VOLTAGE TRANSISTOR

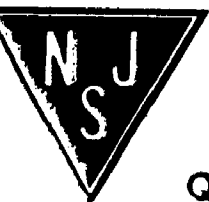
TJ-202

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| | SYMBOL | 2N6557 | 2N6558 | 2N6559 | UNIT |
|---|----------------|--------|-------------|--------|--------------------|
| Collector-Base Voltage | V_{CB0} | 250 | 300 | 350 | V |
| Collector Emitter Voltage | V_{CE0} | 250 | 300 | 350 | V |
| Emitter Base Voltage | V_{EBO} | | 6.0 | | V |
| Collector Current | I_C | | 0.5 | | A |
| Collector Current (PEAK) | I_{CM} | | 0.7 | | A |
| Base Current | I_B | | 250 | | mA |
| Power Dissipation | P_D | | 2.0 | | W |
| Power Dissipation ($T_C=25^\circ\text{C}$) | P_D | | 10 | | W |
| Operating and Storage Junction Temperature | T_J, T_{stg} | | -65 TO +150 | | $^\circ\text{C}$ |
| Thermal Resistance | θ_{JA} | | 62.5 | | $^\circ\text{C/W}$ |
| Thermal Resistance | θ_{JC} | | 12.5 | | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| | | 2N6557 | | 2N6558 | | 2N6559 | | UNIT |
|---------------|--|--------|------|--------|------|--------|------|---------------|
| | | MIN | MAX | MIN | MAX | MIN | MAX | |
| I_{CBO} | $V_{CB}=150\text{V}$ | | 0.2 | | - | | - | μA |
| I_{CBO} | $V_{CB}=200\text{V}$ | | - | | 0.2 | | - | μA |
| I_{CBO} | $V_{CB}=250\text{V}$ | | - | | - | | 0.2 | μA |
| I_{EBO} | $V_{BE}=5.0$ | | 0.1 | | 0.1 | | 0.1 | μA |
| BV_{CBO} | $I_C=100\mu\text{A}$ | 250 | | 300 | | 350 | | V |
| BV_{CE0} | $I_C=1.0\text{mA}$ | 250 | | 300 | | 350 | | V |
| BV_{EBO} | $I_E=100\mu\text{A}$ | 6.0 | | 6.0 | | 6.0 | | V |
| $V_{CE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | | 0.6 | | 0.6 | | 0.6 | V |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$ | | 1.5 | | 1.5 | | 1.5 | V |
| $V_{BE(ON)}$ | $V_{CE}=10\text{V}, I_C=30\text{mA}$ | | 0.85 | | 0.85 | | 0.85 | V |
| h_{FE} | $V_{CE}=10\text{V}, I_C=1.0\text{mA}$ | 25 | | 25 | | 25 | | |
| h_{FE} | $V_{CE}=10\text{V}, I_C=30\text{mA}$ | 40 | 180 | 40 | 180 | 40 | 180 | |
| f_T | $V_{CE}=20\text{V}, I_C=10\text{mA}, f=20\text{MHz}$ | 45 | 200 | 45 | 200 | 45 | 200 | MHz |
| C_{ob} | $V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$ | | 3.0 | | 3.0 | | 3.0 | pF |



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Quality Semi-Conductors